Ref #	Hits	Search Query	DBs	Default Operator	Piurals	Time Stamp
		S111 and (ingaas gainas gallium near indium near (arsenide arsenic)) same strain and (algaas gaalas aluminum near gallium (arsenic arsenide)) same electron and (hemt high near electron near mobility near transistor transistor) and	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:41
		(ingaas indium near gallium near (arsenic arsenide) and "77" near k same nm and S95 and (algaas aluminum near gasllium near (arsenic arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:30
		S7 and hemt same strain and ingaas and algaas and	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:41
L1	2	("6849866").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 21:14
L2	22	(ingaas gainas indium near2 gallium near2 arsenide) same (2-deg 2deg two-dimensional two near dimensional) near gas and wavelength and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:02
L3		L2 and "20030006407".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 21:15
L4	1	("5010374").PN. OR ("6849866"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 21:18

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r			r			
L5	30	(US-20040069991-\$).did. or (US-5625204-\$ or US-5751029-\$ or US-5900653-\$ or US-5258632-\$ or US-5650642-\$ or US-6307221-\$ or US-5773853-\$ or US-5404032-\$ or US-5406099-\$ or US-5945690-\$ or US-6593603-\$ or US-6639254-\$ or US-5825796-\$ or US-5569954-\$ or US-5550388-\$ or US-5751027-\$ or US-6177684-\$ or US-5196359-\$ or US-6242293-\$ or US-4688068-\$ or US-5486705-\$ or US-5832018-\$ or US-6229153-\$ or US-5762706-\$ or US-5441913-\$ or US-4780877-\$). did. or (US-5015099-\$ or US-5126803-\$ or US-5585957-\$). did.	US-PGPUB; USPAT	OR	ON	2006/09/20 21:51
L6		I5 and electron near mobility	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 21:52
L7	20	I5 and electron near mobility and ingaas and algaas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 21:52
L8	3	("4830980"   "4908325"   "5118637").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 22:00
L9	8	"cm.sup.2 /Vs"	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 22:01
L10	244970	"cm.sup.2"	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 22:01
L11	260	(ingaas gainas indium near2 gallium near2 arsenide) same "cm.sup.2"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:01
L12	6	(ingaas gainas indium near2 gallium near2 arsenide) same (2-deg 2deg two-dimensional two near dimensional) near gas and transistor and "cm.sup.2"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:02

L13	23721359	@ad<"20021225" @rlad<"20021225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:02
L14	5	(ingaas gainas indium near2 gallium near2 arsenide) same (2-deg 2deg two-dimensional two near dimensional) near gas and transistor and "cm.sup.2" and L13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:05
L15	2	(ingaas gainas indium near2 gallium near2 arsenide) same (2-deg 2deg two-dimensional two near dimensional) near gas and transistor and "cm.sup.2" and L13 and algaas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:09
L16	6	("4705361"   "4734750"   "4745447").PN. OR ("4958203"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 22:08
L17	17262	aluminum near2 gallium near2 arsenide algaas gaalas	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 22:09
L18	537	(ingaas gainas indium near2 gallium near2 arsenide) and l17 and transistor and "cm.sup.2" and L13 and algaas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:10
L19	636	(ingaas gainas indium near2 gallium near2 arsenide) and l17 and transistor and "cm.sup.2" and L13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	.2006/09/20 22:45
L20	7	(ingaas gainas indium near2 gallium near2 arsenide) and l17 and transistor and "300" near "k" same mobility and L13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:37
L21	2	"5060030".pn. and mobility	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 22:44

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L22	2	"6639254".pn. and mobility	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/09/20 22:44
L23	125	(ingaas gainas indium near2 gallium near2 arsenide) and l17 and transistor and "cm.sup.2" same mobility and L13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 23:18
L24	0	"5258632".pn. and "300" near k	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 23:18
L25	0	"5258632".pn. and ("300" near k 300k)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 23:18
S1	1233	257/192.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:42
S2	1122	257/194.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:42
S3	193	257/195.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:42
54	538	257/190.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:42

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S5	363	257/20.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:43
S6	2724	S1 or S2 or S3 or S4 or S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:44
S7	2351	S6 and @ad<"20021225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:46
S8	209	S7 and hemt and ingaas and algaas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:47
S9	13	S7 and hemt same strain and ingaas and algaas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:55
S10	6	S7 and hemt same strain and ingaas and algaas and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:55
S11	6	S7 and hemt same strain and ingaas and algaas and wavelength and nm	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:56
S12	5	S7 and hemt same strain and ingaas and algaas and wavelength and nm and emission	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 15:05
S13	1	(("6163599") or ("0684959") or ("2001210819") or ("0621106") or ("2708863")).PN.	JPO	OR	OFF	2006/02/13 15:06

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S14	0	("6163599").PN.	JPO	OR	OFF	2006/02/13 15:06
S15	0	("6-163599").PN.	JPO	OR	OFF	2006/02/13 15:06
S16	2	("6163599").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/13 15:07
S17	0	(nec near corp).as. and "19940610".rlpd.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 15:38
S18	403329	(nec near corp).as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 15:38
S19	245778	(nec near corp).as.	JPO	OR	ON	2006/02/13 15:38
S20	245778	(nec near corp).as. and jp "6163599"	JPO	OR	ON	2006/02/13 15:39
S21	0	(nec near corp).as. and jp and "6163599"	JPO	OR	ON	2006/02/13 15:39
S22	245778	(nec near corp).as. "6163599"	JPO	OR	ON	2006/02/13 15:39
S23	0	(nec near corp).as. and "6163599"	JPO	OR	ON	2006/02/13 15:39
S24	0	(nec near corp).as. and "6-163599"	JPO	OR	ON	2006/02/13 15:39
S25	0	"6-163599"	JPO	OR	ON	2006/02/13 15:40
S26	299	(nec near corp).as. and "19940610"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 15:40
S27	0	(nec near corp).as. and "19940610" and "163599"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 15:41
S28	299	(nec near corp).as. and "19940610"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 16:07

S29	29	(nec near corp).as. and (negishi near hitoshi).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 16:08
S30	0	(nec near corp).as. and (negishi near hitoshi).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/13 16:08
S31	5	(negishi near hitoshi).in.	US-PGPUB; USPAT; USOCR	OR .	ON	2006/02/13 16:08
532	3	("5400739"   "5490880"   "5625204").PN. OR ("6099640"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/13 16:18
S33	8	fujitsu.as. and (saito near junji).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/13 16:22
S34	2	hitachi.as. and ((sasaki near yukio). in. or (tsuchiya near tadaitsu))	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/13 16:26
S35	0	hitachi.as. and (tsuchiya near tadaitsu).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/13 16:27
S36	0	hitachi.as. and (tadaitsu).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/13 16:27
S37	0	(tadaitsu).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/13 16:28
S38	33	(sawada near minoru).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/13 16:28
S39	18	(sawada near minoru).in. and sanyo.as.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 14:44
S40	2	("6639254").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 15:09
S41	9	algaas same ingaas near strain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:13

S42	632	(ishikawa near makoto).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 15:13
S43	114	(ishikawa near makoto).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:13
S44	2	(ishikawa near makoto).in. and hemt	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:14
S45	0	(ishikawa near makoto).in. and nec. as.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:14
S46	114	(ishikawa near makoto).in.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:15
S47	0	JP02254412	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:15
S48	7	"2254412"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:39
S49	0	(feng near zhao).in. and algaas and ingaas	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:40
S50	5	(zhao).in. and algaas and ingaas	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:41
S51	0	(strau).in. and algaas and ingaas	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:41
S52		(straub).in. and algaas and ingaas	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:41
S53	0	(bernklau).in. and algaas and ingaas	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 15:41
S54	12	(US-5825796-\$ or US-5945690-\$ or US-6639254-\$ or US-5569954-\$ or US-5625204-\$ or US-5773853-\$ or US-5751029-\$ or US-5650642-\$ or US-5404032-\$ or US-5258632-\$ or US-5406099-\$). did.	USPAT	OR	ON	2006/02/14 16:29

S55	10	S54 and mobility	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 16:30
S56	10	S54 and electron near mobility	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 16:31
S57	4	algaas same ingaas near strain and electron near mobility	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 16:31
S58	4	algaas same ingaas near strain and electron near mobility and @ad<"20021225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/14 16:32
S59	28	("4742379"   "4792832"   "5021857"   "5041393"   "5060030"   "5091759"   "5140386"   "5196359"   "5270228"   "5272109"   "5285087"   "5324682"   "5330932"   "5364816"   "5372675"   "5504353"   "5514605"   "5521404"   "5550388"   "5641977"   "5760427"   "5770525"   "5811844"   "5900653"   "6060402").PN. OR ("6307221"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 17:49
S60	24	S59 and mobility	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 17:49
S61	23	S59 and mobility and @ad<"20021225"	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/14 17:50
S62	3721	ingaas same algaas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 19:15

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S63	23717685	@ad<"20021225" @rlad<"20021225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 18:57
S64	896179	fet hemt field near effect near transistor or high near electron near mobility near (field near effect near transistor fet) transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 18:59
S65	514599	strain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 18:59
S66	571	strain near channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/09/12 18:59
S67	7	S62 and S63 and S64 and S66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 19:00
S68	4483	(ingaas gainas) same (algaas gaalas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 19:19
S69	7	S68 and S63 and S64 and S66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 19:17
S70	5626	(ingaas gainas gallium near indian near (arsenide arsenic)) same (algaas gaalas aluminum near galium (arsenic arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 19:21

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S71	. 8	S70 and S63 and S64 and S66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 19:22
S72	9019	(ingaas gainas gallium near indium near (arsenide arsenic)) same (algaas gaalas aluminum near gallium (arsenic arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:39
S73	8	S72 and S63 and S64 and S66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/09/12 19:22
S74	6366	hemt or (high near electron near mobility near transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:41
S75	872	channel near5 (InGaAs or GaAsIn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:42
S76	2820	(n-type near2 AlGaAs) or n-AlGaAs or ((electron near supply\$3) near5 AlGaAs)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:42
S77	164	InGaAs same (peak near5 wavelength)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:43
S78	3	S74 and S75 and S76 and S77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:43

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S79	5	S75 and S76 and S77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:43
S80	872	S75 andl3 and (peak near5 wavelength)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:43
S81	225	S75 and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:43
S82	15	S81 and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:43
S83	884	S76 and (InGaAs or GaAsIn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:43
S84	30	S83 and (peak near wavelength)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:44
S85	435212	"257"/\$.ccls. "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:44
S86	5740	257/187,192,194,E31.053,E33.027, E33.032,E33.053,E21.403,E21.407. ccls. 438/22,46.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/09/19 17:45

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S87	27011996	@ad<"20050623"	US-PGPUB;	OR	ON	2006/09/19 17:45
		@rlad<"20050623"	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			
S88	23721359	@ad<"20021225" @rlad<"20021225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON.	2006/09/19 17:46
S89	2	S78 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:58
S90	13999	ingaas (indium near gallium near arsenic) same "77" near k with nm	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:59
S91	13999	ingaas (indium near gallium near arsenic) same "77" near k with nm and S85 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OŅ	2006/09/19 18:04
S92	0	(ingaas indium near gallium near arsenic) same "77" near k with nm and S85 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:05
S93	0	(ingaas indium near gallium near arsenic) same "77" near k same nm and S85 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:05
S94 	1	(ingaas indium near gallium near arsenic) same "77" near k same nm and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:12

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S95	23721359	@ad<"20021225" @rlad<"20021225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:12
S96	20	(ingaas indium near gallium near arsenic) and "77" near k same nm and S95	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:12
S97	18	(ingaas indium near gallium near arsenic) and "77" near k same nm and S95 and algaas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:12
S98	18	(ingaas indium near gallium near arsenic) and "77" near k same nm and S95 and (algaas aluminum near gasllium near arsenic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:29
S99	18	(ingaas indium near gallium near (arsenic arsenide)) and "77" near k same nm and S95 and (algaas aluminum near gasllium near (arsenic arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:30
S10 0	17	(ingaas indium near gallium near (arsenic arsenide)) and "77" near k same wavelength and S95 and (algaas aluminum near gasllium near (arsenic arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 19:14
S10 1	17	S100 not "I8"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:31
S10 2	4	S100 not S99	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:32

S10 3	22	(ingaas indium near gallium near (arsenic arsenide)) and "77" near k same (wavelength ".mu.m" nm) and S95 and (algaas aluminum near gasllium near (arsenic arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 19:17
S10 4	0	".mu.m"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 19:17
S10 5	0	".mu.m"\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:25
S10 6	2	"6573527".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ,	ON	2006/09/20 10:26
S10 7	0	"6573527".pn. and hemt and strain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:26
S10 8	. 0	"6573527".pn. and hemt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:26
S10 9	1	"6573527".pn. and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:27
S11 0	11104	(ingaas gainas gallium near indium near (arsenide arsenic)) and (algaas gaalas aluminum near gallium (arsenic arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:39

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S11 1	23721359	@ad<"20021225" @rlad<"20021225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:41
S11 2	266	S111 and (ingaas gainas gallium near indium near (arsenide arsenic)) same strain and (algaas gaalas aluminum near gallium (arsenic arsenide)) same electron and (hemt high near electron near mobility near transistor transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 11:46
S11 3	29	S111 and (ingaas gainas gallium near indium near (arsenide arsenic)) same strain and (algaas gaalas aluminum near gallium (arsenic arsenide)) same electron and (hemt high near electron near mobility near transistor transistor) and graph	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:41
S11 4	112	S111 and (ingaas gainas gallium near indium near (arsenide arsenic)) same strain and (algaas gaalas aluminum near gallium (arsenic arsenide)) same electron and (hemt high near electron near mobility near transistor transistor) and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:41
S11 5	6	S111 and (ingaas gainas gallium near indium near (arsenide arsenic)) same strain and (algaas gaalas aluminum near gallium (arsenic arsenide)) same electron and (hemt high near electron near mobility near transistor transistor) and "77" near k	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:43
S11 6	14	("4830980"   "4908325"   "5118637").PN. OR ("5196359"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 10:48
S11 7	9	("3821783"   "4688068"   "4872046"   "5016252"   "5212404"   "5263040").PN. OR ("5569954"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 11:00
S11 8	9	("4894836"   "4974231"   "5146466").PN. OR ("5263040"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/20 11:09

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S11 9	76	S111 and (ingaas gainas gallium near indium near (arsenide arsenic)) and (algaas gaalas aluminum near gallium (arsenic arsenide)) and "77" near k	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 11:59
S12 0	40	S111 and (ingaas gainas gallium near indium near (arsenide arsenic)) and (algaas gaalas aluminum near gallium (arsenic arsenide)) and "77" near k same (wavelength peak pl nm emision)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 11:48
S12 1	12	hemt and ingaas same channel and emission near peak	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:22
S12 2	11	hemt and ingaas same channel and emission near peak near wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:01
S12 3	, <b>11</b>	hemt and ingaas same channel and emission near3 peak near wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:01
S12 4	11	hemt and ingaas same channel and emission near5 peak near wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:03
S12 5	11	hemt and ingaas same channel and emission near5 peak near5 wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:03
S12 6	10	hemt and ingaas same channel and emission near5 peak near5 wavelength and S111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:26

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S12 7	. 2	("5,060,030").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 12:22
S12 8	105	ingaas and emission near5 peak near5 wavelength and S111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:26
S12 9	127	(ingaas indium near gallium near arsenide) and emission near5 peak near5 wavelength and S111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:29
S13 0	279	(ingaas indium near gallium near arsenide) and emission near5 peak and S111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:29
S13 1	116	(ingaas indium near gallium near arsenide) and emission near5 peak and S111 and graph	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/09/20 12:37
S13 2	50	(ingaas indium near gallium near arsenide) and emission near5 peak and S111 and graph and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/09/20 16:38
S13 3	2	("6639254").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 16:38
S13 4	2	S133 and hemt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 16:42

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T			<u> </u>			2004/52/22
S13 5	849291	transistor ingaas same channel and peak near wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 16:43
S13 6	23	transistor and ingaas same channel and peak near wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 16:50
S13 7	0	transistor and ingaas same (two-dimensional two near dimensional) near gas and peak near wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 16:52
S13 8	18	transistor and ingaas same (two-dimensional two near dimensional) near gas and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 16:52
S13 9	20	ingaas same (two-dimensional two near dimensional) near gas and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 16:57
S14 0	73	2-deg	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 16:56
S14 1	21	ingaas same (2-deg two-dimensional two near dimensional) near gas and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 16:57
S14 2	21	(ingaas gainas indium near2 gallium near2 arsenide) same (2-deg two-dimensional two near dimensional) near gas and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 17:01

S14 3	. 25	(ingaas gainas indium near2 gallium near2 arsenide) same (2-deg 2deg two-dimensional two near dimensional) near gas and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 17:10
S14 4	22	(ingaas gainas indium near2 gallium near2 arsenide) same (2-deg 2deg two-dimensional two near dimensional) near gas and wavelength and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 17:28
S14 5	2	("6849866").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 21:06

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